AMENDMENT TO THE CLAIMS:

Claims 1. (original) A method for fabricating a semiconductor device having at least one thin film transistor comprising a channel region and a gate electrode, comprising the steps of:

forming a semiconductor film comprising an amorphous silicon over a substrate; and

irradiating said semiconductor film with a laser light having a rectangular irradiation area while relatively moving said laser light along a scan direction,

wherein said scan direction is parallel to said channel region.

Claims 2-7 (canceled).

Claim 8. (original) The method of claim 1, wherein said thin film transistor is used as one of a column driver and a scan driver.

Claim 9. (canceled)

Claim 10. (original) A method for fabricating a thin film transistor device having a polycrystalline semiconductor thin film to form a channel regions, and a gate electrode which intersects the channel region, comprising the steps of:

providing a structure comprising a semiconductor thin film separated by a gate insulating layer from a gate electrode on an insulating substrate; and

irradiating the semiconductor thin film with a laser light having a rectangular irradiation area while relatively moving said laser light along a scan direction which is parallel to the channel region.

Claim 11. (canceled)

Claim 12. (original) The method of claim 10, wherein said irradiating step comprises moving the laser light.

Claims 13. (original) The method of claim 10, wherein said irradiating step comprises partially overlapping irradiation of the laser light.

Claims 14-18 (canceled)

Claim 19. (original) The method of claim 10, wherein said thin film transistor is used as one of a column driver and a scan driver.

Claim 20. (canceled)

Claim 21. (original) A method for fabricating a thin film transistor device having a polycrystalline semiconductor thin film to form a channel region, and a gate electrode which intersects the channel region, comprising the steps of:

providing a structure comprising a semiconductor thin film separated by a gate insulating layer from a gate electrode on an insulating substrate;

introducing a dopant impurity to said semiconductor thin film; and

irradiating the semiconductor thin film with a laser light having a rectangular irradiation area while relatively moving said laser light along a scan direction which is parallel to the channel region in order to activate said dopant impurity.

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Claim 22. (canceled)

Claim 23. (original) The method of claim 21, wherein said irradiating step comprises moving the laser light.

Claim 24. (original) The method of claim 21, wherein said irradiating step comprises partially overlapping the laser light.

Claims 25 – 29 (canceled).

Claims 30. (original) The method of claim 21, wherein said thin film transistor is used as one of a column driver and a scan driver.

Claim 31. (original) A method for fabricating a thin film transistor device having a polycrystalline semiconductor thin film to form a channel region, and a gate electrode which intersects the channel region, comprising the steps of:

forming a structure comprising an amorphous semiconductor thin film separated by a gate insulating layer from a gate electrode on an insulating substrate; and

irradiating the amorphous semiconductor thin film with an energy beam having a rectangular irradiation area to convert the amorphous semiconductor thin film into a polycrystalline semiconductor thin film while relatively moving said energy beam along a scan direction which is orthogonal to the gate electrode and is parallel to the channel region.

Claim 32. (original) A method according to claim 31, wherein said irradiation step is a process for irradiating an amorphous semiconductor thin film to form a polycrystalline semiconductor thin film of the thin film transistor connected to a pixel electrode formed on the insulating substrate.

Claim 33. (original) A method according to claim 31, wherein said irradiation step is a process for irradiating an amorphous semiconductor thin film to form a polycrystalline semiconductor thin film of the thin film transistor comprised of peripheral driving circuit for an active matrix array.

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Claim 34. (original) A method according to claim 31, wherein said irradiation step is performed by moving the energy beam.

Claim 35. (original) A method according to 31, wherein said irradiation step is performed by partially overlapping irradiation of energy beam.

Claim 36. (original) A method according to claim 31, further comprising steps of forming source and drain regions which comprise doping an impurity to the polycrystalline semiconductor thin film and activating the doped impurity by irradiating an energy beam.

Claim 37. (previously presented) A method for fabricating a semiconductor device having at least one thin film transistor comprising a channel region and a gate electrode, comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate; and

irradiating said semiconductor film with a laser light having an elongated irradiation area while relatively moving said laser light along a scan direction,

wherein said scanning direction is parallel to said channel region.

Claims 38 -43 (canceled)

Claim 44. (previously presented) The method of claim 37, wherein said thin film transistor is one of a column driver and a scan driver.

Claim 45. (canceled)

Claim 46. (previously presented) A method for fabricating a thin film transistor device having a polycrystalline semiconductor thin film to form a channel region, and a gate electrode which intersects the channel region, comprising the steps of:

providing a structure comprising a semiconductor thin film separated by a gate insulating layer from a gate electrode on an insulating substrate; and

irradiating the semiconductor thin film with a laser light having an elongated irradiation area while relatively moving said laser light along a scan direction which is parallel to the channel region.

Claim 47. (canceled)

Claim 48. (previously presented) The method of claim 46, wherein said irradiating step comprises moving the laser light.

Claim 49. (previously presented) The method of claim 46, wherein said irradiating step comprises partially overlapping irradiation of the laser light.

Claims 50-54 (canceled)

Claims 55. (previously presented) The method of claim 46, wherein said thin film transistor is one of a column driver and a scan driver.

Claim 56. (canceled)

Claim 57. (previously presented) A method for fabricating a thin film transistor device having a polycrystalline semiconductor thin film to form a channel region, and a gate electrode which intersects the channel region, comprising the steps of:

providing a structure comprising a semiconductor thin film separated by a gate insulating layer from a gate electrode on an insulating substrate;

introducing a dopant impurity to said semiconductor thin film; and

irradiating the semiconductor thin film with a laser light having an elongated irradiation area while relatively moving said laser light along a scan direction which is parallel to the channel region in order to activate said dopant impurity.

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Claim 58. (canceled)

Claim 59. (previously presented) The method of claim 57, wherein said irradiating step comprises moving the laser light.

Claim 60. (previously presented) The method of claim 57, wherein said irradiating step comprises partially overlapping the laser light.

Claims 61-65 (canceled)

Claims 66. (previously presented) The method of claim 57, wherein said thin film transistor is one of a column driver and a scan driver.

Claim 67. (previously presented) A method for fabricating a thin film transistor device having a polycrystalline semiconductor thin film to form a channel region, and a gate electrode which intersects the channel region, comprising the steps of:

forming a structure comprising an amorphous semiconductor thin film separated by a gate insulating layer from a gate electrode on an insulating substrate;

irradiating the amorphous semiconductor thin film with an energy beam having an elongated irradiation area to convert the amorphous semiconductor thin film into a polycrystalline semiconductor thin film while relatively moving said energy beam along a scan direction which is orthogonal to the gate electrode and is parallel to the channel region.

Claim 68. (previously presented) A method according to claim 67, wherein said irradiation step is a process for irradiating an amorphous semiconductor thin film to form a polycrystalline semiconductor thin film of the thin film transistor connected to a pixel electrode formed on the insulating substrate.

Claim 69. (previously presented) A method according to claim 67, wherein said irradiation step is a process for irradiating an amorphous semiconductor thin film to form a polycrystalline semiconductor thin film of the thin film transistor comprised of a peripheral driving circuit for an active matrix display.

Claim 70. (previously presented) A method according to claim 67, wherein said irradiation step is performed by moving the energy beam.

Claim 71. (previously presented) A method according to claim 67, wherein said irradiation step is performed by partially overlapping irradiation of the energy beam.

Claim 72. (previously presented) A method according to claim 67, further comprising steps of:

forming source and drain regions which comprise doping an impurity to the polycrystalline semiconductor thin film; and

activating the doped impurity by irradiating an energy beam.

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